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### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	10K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l152c8u6">https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l152c8u6</a>

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# 1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L151x6/8/B and STM32L152x6/8/B ultra-low-power ARM® Cortex®-M3 based microcontrollers product line.

The ultra-low-power STM32L151x6/8/B and STM32L152x6/8/B family includes devices in 3 different package types: from 48 to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L151x6/8/B and STM32L152x6/8/B microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, Wired and wireless sensors, Video intercom
- Utility metering

This STM32L151x6/8/B and STM32L152x6/8/B datasheet should be read in conjunction with the STM32L1xxxx reference manual (RM0038).

The document "Getting started with STM32L1xxxx hardware development" AN3216 gives a hardware implementation overview. Both documents are available from the STMicroelectronics website [www.st.com](http://www.st.com).

For information on the ARM® Cortex®-M3 core please refer to the Cortex®-M3 Technical Reference Manual, available from the [www.arm.com](http://www.arm.com) website.

*Figure 1* shows the general block diagram of the device family.

**Caution:** This datasheet does not apply to STM32L15xx6/8/B-A covered by a separate datasheet.

### Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L151x6/8/B and STM32L152x6/8/B devices embed a nested vectored interrupt controller able to handle up to 45 maskable interrupt channels (not including the 16 interrupt lines of Cortex<sup>®</sup>-M3) and 16 priority levels.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving*, higher-priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

## 3.3 Reset and supply management

### 3.3.1 Power supply schemes

- $V_{DD} = 1.65$  to  $3.6$  V: external power supply for I/Os and the internal regulator. Provided externally through  $V_{DD}$  pins.
- $V_{SSA}$ ,  $V_{DDA} = 1.65$  to  $3.6$  V: external analog power supplies for ADC, reset blocks, RCs and PLL (minimum voltage to be applied to  $V_{DDA}$  is  $1.8$  V when the ADC is used).  $V_{DDA}$  and  $V_{SSA}$  must be connected to  $V_{DD}$  and  $V_{SS}$ , respectively.

### 3.3.2 Power supply supervisor

The device has an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

The device exists in two versions:

- The version with BOR activated at power-on operates between  $1.8$  V and  $3.6$  V.
- The other version without BOR operates between  $1.65$  V and  $3.6$  V.

After the  $V_{DD}$  threshold is reached ( $1.65$  V or  $1.8$  V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the  $V_{DD}$  min value becomes  $1.65$  V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from  $1.8$  V whatever the power ramp-up phase before it reaches  $1.8$  V. When BOR is not active at power-up, the power ramp-up should guarantee that  $1.65$  V is reached on  $V_{DD}$  at least  $1$  ms after it exits the POR area.

### 3.4 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low power modes and ensures clock robustness. It features:

- **Clock prescaler:** to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching:** clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management:** to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **Master clock source:** three different clock sources can be used to drive the master clock:
  - 1-24 MHz high-speed external crystal (HSE), that can supply a PLL
  - 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
  - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65.5 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz) with a consumption proportional to speed, down to 750 nA typical. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a  $\pm 0.5\%$  accuracy.
- **Auxiliary clock source:** two ultra-low-power clock sources that can be used to drive the LCD controller and the real-time clock:
  - 32.768 kHz low-speed external crystal (LSE)
  - 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.
- **RTC and LCD clock sources:** the LSI, LSE or HSE sources can be chosen to clock the RTC and the LCD, whatever the system clock.
- **USB clock source:** the embedded PLL has a dedicated 48 MHz clock output to supply the USB interface.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 2.1 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS):** this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.
- **Clock-out capability (MCO: microcontroller clock output):** it outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See [Figure 2](#) for details on the clock tree.

### 3.5 Low power real-time clock and backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are made automatically. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes.

- The programmable wakeup time ranges from 120  $\mu$ s to 36 hours
- Stop mode consumption with LSI and Auto-wakeup: 1.2  $\mu$ A (at 1.8 V) and 1.4  $\mu$ A (at 3.0 V)
- Stop mode consumption with LSE, calendar and Auto-wakeup: 1.3  $\mu$ A (at 1.8V), 1.6  $\mu$ A (at 3.0 V)

The RTC can be calibrated with an external 512 Hz output, and a digital compensation circuit helps reduce drift due to crystal deviation.

There are twenty 32-bit backup registers provided to store 80 bytes of user application data. They are cleared in case of tamper detection.

### 3.6 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated AFIO registers. All GPIOs are high current capable. The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to the AHB with a toggling speed of up to 16 MHz.

#### External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 23 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 83 GPIOs can be connected to the 16 external interrupt lines. The 7 other lines are connected to RTC, PVD, USB or Comparator events.

### 3.15.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit down-counter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

## 3.16 Communication interfaces

### 3.16.1 I<sup>2</sup>C bus

Up to two I<sup>2</sup>C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support dual slave addressing (7-bit only) and both 7- and 10-bit addressing in master mode. A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SM Bus 2.0/PM Bus.

### 3.16.2 Universal synchronous/asynchronous receiver transmitter (USART)

All USART interfaces are able to communicate at speeds of up to 4 Mbit/s. They provide hardware management of the CTS and RTS signals and are ISO 7816 compliant. They support IrDA SIR ENDEC and have LIN Master/Slave capability.

All USART interfaces can be served by the DMA controller.

### 3.16.3 Serial peripheral interface (SPI)

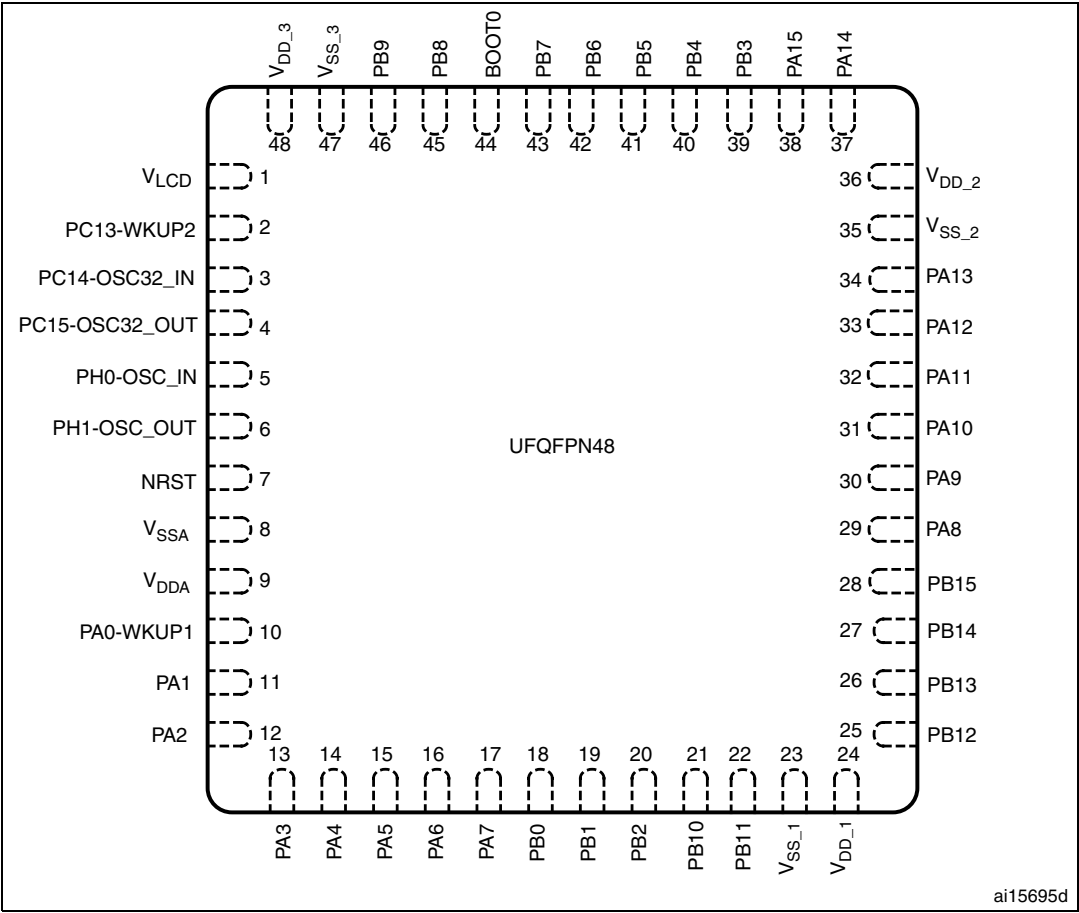
Up to two SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

Both SPIs can be served by the DMA controller.

### 3.16.4 Universal serial bus (USB)

The STM32L151x6/8/B and STM32L152x6/8/B devices embed a USB device peripheral compatible with the USB full speed 12 Mbit/s. The USB interface implements a full speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and supports suspend/resume. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).

Figure 8. STM32L15xCx UFQFPN48 pinout



1. This figure shows the package top view.



Table 8. STM32L151x6/8/B and STM32L152x6/8/B pin definitions (continued)

Pins					Pin name	Pin type <sup>(1)</sup>	I/O structure	Main function <sup>(2)</sup> (after reset)	Pins functions	Additional functions
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UFQFPN48					Alternate functions	
35	26	F5	M5	18	PB0	I/O	TC	PB0	TIM3_CH3/LCD_SEG5	ADC_IN8/ COMP1_INP/ VREF_OUT
36	27	G5	M6	19	PB1	I/O	FT	PB1	TIM3_CH4/LCD_SEG6	ADC_IN9/ COMP1_INP/ VREF_OUT
37	28	G6	L6	20	PB2	I/O	FT	PB2/BOOT1	BOOT1	-
38	-	-	M7	-	PE7	I/O	TC	PE7	-	ADC_IN22/ COMP1_INP
39	-	-	L7	-	PE8	I/O	TC	PE8	-	ADC_IN23/ COMP1_INP
40	-	-	M8	-	PE9	I/O	TC	PE9	TIM2_CH1_ETR	ADC_IN24/ COMP1_INP
41	-	-	L8	-	PE10	I/O	TC	PE10	TIM2_CH2	ADC_IN25/ COMP1_INP
42	-	-	M9	-	PE11	I/O	FT	PE11	TIM2_CH3	-
43	-	-	L9	-	PE12	I/O	FT	PE12	TIM2_CH4/SPI1_NSS	-
44	-	-	M10	-	PE13	I/O	FT	PE13	SPI1_SCK	-
45	-	-	M11	-	PE14	I/O	FT	PE14	SPI1_MISO	-
46	-	-	M12	-	PE15	I/O	FT	PE15	SPI1_MOSI	-
47	29	G7	L10	21	PB10	I/O	FT	PB10	I2C2_SCL/USART3_TX/ TIM2_CH3/LCD_SEG10	-
48	30	H7	L11	22	PB11	I/O	FT	PB11	I2C2_SDA/USART3_RX/ TIM2_CH4/LCD_SEG11	-
49	31	D6	F12	23	V <sub>SS_1</sub>	S	-	V <sub>SS_1</sub>	-	-
50	32	E6	G12	24	V <sub>DD_1</sub>	S	-	V <sub>DD_1</sub>	-	-
51	33	H8	L12	25	PB12	I/O	FT	PB12	SPI2_NSS/I2C2_SMBA/ USART3_CK/ LCD_SEG12/TIM10_CH1	ADC_IN18/ COMP1_INP
52	34	G8	K12	26	PB13	I/O	FT	PB13	SPI2_SCK/USART3_CTS/ LCD_SEG13/ TIM9_CH1	ADC_IN19/ COMP1_INP

Table 14. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{PVD0}$	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	V
		Rising edge	1.88	1.94	1.99	
$V_{PVD1}$	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
$V_{PVD2}$	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
$V_{PVD3}$	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
$V_{PVD4}$	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
$V_{PVD5}$	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
$V_{PVD6}$	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
$V_{hyst}$	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results.

2. Valid for device version without BOR at power up. Please see option "T" in Ordering information scheme for more details.

Table 20. Current consumption in Low power run mode

Symbol	Parameter	Conditions			Typ	Max (1)	Unit
$I_{DD}$ (LP Run)	Supply current in Low power run mode	All peripherals OFF, code executed from RAM, Flash switched OFF, $V_{DD}$ from 1.65 V to 3.6 V	MSI clock, 65 kHz $f_{HCLK} = 32$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	9	12	$\mu\text{A}$
				$T_A = 85\text{ }^{\circ}\text{C}$	17.5	24	
				$T_A = 105\text{ }^{\circ}\text{C}$	31	46	
			MSI clock, 65 kHz $f_{HCLK} = 65$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	14	17	
				$T_A = 85\text{ }^{\circ}\text{C}$	22	29	
				$T_A = 105\text{ }^{\circ}\text{C}$	35	51	
			MSI clock, 131 kHz $f_{HCLK} = 131$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	37	42	
				$T_A = 55\text{ }^{\circ}\text{C}$	37	42	
				$T_A = 85\text{ }^{\circ}\text{C}$	37	42	
				$T_A = 105\text{ }^{\circ}\text{C}$	48	65	
		All peripherals OFF, code executed from Flash, $V_{DD}$ from 1.65 V to 3.6 V	MSI clock, 65 kHz $f_{HCLK} = 32$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	24	32	
				$T_A = 85\text{ }^{\circ}\text{C}$	33	42	
				$T_A = 105\text{ }^{\circ}\text{C}$	48	64	
			MSI clock, 65 kHz $f_{HCLK} = 65$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	31	40	
				$T_A = 85\text{ }^{\circ}\text{C}$	40	48	
				$T_A = 105\text{ }^{\circ}\text{C}$	54	70	
			MSI clock, 131 kHz $f_{HCLK} = 131$ kHz	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	48	58	
				$T_A = 55\text{ }^{\circ}\text{C}$	54	63	
				$T_A = 85\text{ }^{\circ}\text{C}$	56	65	
				$T_A = 105\text{ }^{\circ}\text{C}$	70	90	
$I_{DD}$ Max (LP Run) <sup>(2)</sup>	Max allowed current in Low power run mode	$V_{DD}$ from 1.65 V to 3.6 V	-	-	-	200	

1. Guaranteed by characterization results, unless otherwise specified.
2. This limitation is related to the consumption of the CPU core and the peripherals that are powered by the regulator. Consumption of the I/Os is not included in this limitation.

Table 23. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ <sup>(1)</sup>	Max <sup>(1)(2)</sup>	Unit
$I_{DD}$ (Standby with RTC)	Supply current in Standby mode with RTC enabled	RTC clocked by LSI (no independent watchdog)	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$ $V_{DD} = 1.8\text{ V}$	0.9	-	$\mu\text{A}$
			$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	1.1	1.8	
			$T_A = 55\text{ }^{\circ}\text{C}$	1.42	2.5	
			$T_A = 85\text{ }^{\circ}\text{C}$	1.87	3	
			$T_A = 105\text{ }^{\circ}\text{C}$	2.78	5	
		RTC clocked by LSE (no independent watchdog) <sup>(3)</sup>	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$ $V_{DD} = 1.8\text{ V}$	1	-	
			$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	1.33	2.9	
			$T_A = 55\text{ }^{\circ}\text{C}$	1.59	3.4	
			$T_A = 85\text{ }^{\circ}\text{C}$	2.01	4.3	
			$T_A = 105\text{ }^{\circ}\text{C}$	3.27	6.3	
$I_{DD}$ (Standby)	Supply current in Standby mode with RTC disabled	Independent watchdog and LSI enabled	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	1.1	1.6	
		Independent watchdog and LSI OFF	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	0.3	0.55	
			$T_A = 55\text{ }^{\circ}\text{C}$	0.5	0.8	
			$T_A = 85\text{ }^{\circ}\text{C}$	1	1.7	
			$T_A = 105\text{ }^{\circ}\text{C}$	2.5	4 <sup>(4)</sup>	
$I_{DD}$ (WU from Standby)	RMS supply current during wakeup time when exiting from Standby mode	-	$V_{DD} = 3.0\text{ V}$ $T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	1	-	

1. The typical values are given for  $V_{DD} = 3.0\text{ V}$  and max values are given for  $V_{DD} = 3.6\text{ V}$ , unless otherwise specified.

2. Guaranteed by characterization results, unless otherwise specified.

3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8pF loading capacitors.

4. Tested in production.

### On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following table. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at  $V_{DD}$  or  $V_{SS}$  (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on

### 6.3.7 Internal clock source characteristics

The parameters given in the following table are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in [Table 13](#).

#### High-speed internal (HSI) RC oscillator

**Table 30. HSI oscillator characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{HSI}$	Frequency	$V_{DD} = 3.0\text{ V}$	-	16	-	MHz
$TRIM^{(1)(2)}$	HSI user-trimmed resolution	Trimming code is not a multiple of 16	-	$\pm 0.4$	0.7	%
		Trimming code is a multiple of 16	-	-	$\pm 1.5$	%
$ACC_{HSI}^{(2)}$	Accuracy of the factory-calibrated HSI oscillator	$V_{DDA} = 3.0\text{ V}$ , $T_A = 25\text{ }^{\circ}\text{C}$	-1 <sup>(3)</sup>	-	1 <sup>(3)</sup>	%
		$V_{DDA} = 3.0\text{ V}$ , $T_A = 0\text{ to }55\text{ }^{\circ}\text{C}$	-1.5	-	1.5	%
		$V_{DDA} = 3.0\text{ V}$ , $T_A = -10\text{ to }70\text{ }^{\circ}\text{C}$	-2	-	2	%
		$V_{DDA} = 3.0\text{ V}$ , $T_A = -10\text{ to }85\text{ }^{\circ}\text{C}$	-2.5	-	2	%
		$V_{DDA} = 3.0\text{ V}$ , $T_A = -10\text{ to }105\text{ }^{\circ}\text{C}$	-4	-	2	%
		$V_{DDA} = 1.65\text{ V to }3.6\text{ V}$ $T_A = -40\text{ to }105\text{ }^{\circ}\text{C}$	-4	-	3	%
$t_{SU(HSI)}^{(2)}$	HSI oscillator startup time	-	-	3.7	6	$\mu\text{s}$
$I_{DD(HSI)}^{(2)}$	HSI oscillator power consumption	-	-	100	140	$\mu\text{A}$

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Tested in production.

#### Low-speed internal (LSI) RC oscillator

**Table 31. LSI oscillator characteristics**

Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(1)}$	LSI frequency	26	38	56	kHz
$D_{LSI}^{(2)}$	LSI oscillator frequency drift $0^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$	-10	-	4	%
$t_{SU(LSI)}^{(3)}$	LSI oscillator startup time	-	-	200	$\mu\text{s}$
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption	-	400	510	nA

1. Tested in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design.

### 6.3.9 Memory characteristics

The characteristics are given at  $T_A = -40$  to  $105\text{ }^{\circ}\text{C}$  unless otherwise specified.

#### RAM memory

**Table 34. RAM and hardware registers**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRM	Data retention mode <sup>(1)</sup>	STOP mode (or RESET)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

#### Flash memory and data EEPROM

**Table 35. Flash memory and data EEPROM characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max <sup>(1)</sup>	Unit
$V_{DD}$	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
$t_{prog}$	Programming / erasing time for byte / word / double word / half- page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	
$I_{DD}$	Average current during whole program/erase operation	$T_A = 25\text{ }^{\circ}\text{C}$ , $V_{DD} = 3.6\text{ V}$	-	300	-	$\mu\text{A}$
	Maximum current (peak) during program/erase operation		-	1.5	2.5	mA

1. Guaranteed by design.

**Table 36. Flash memory, data EEPROM endurance and data retention**

Symbol	Parameter	Conditions	Value			Unit
			Min <sup>(1)</sup>	Typ	Max	
NCYC <sup>(2)</sup>	Cycling (erase / write) Program memory	$T_A = -40\text{ }^{\circ}\text{C}$ to $105\text{ }^{\circ}\text{C}$	10	-	-	kcycles
	Cycling (erase / write) EEPROM data memory		300	-	-	
$t_{RET}$ <sup>(2)</sup>	Data retention (program memory) after 10 kcycles at $T_A = 85\text{ }^{\circ}\text{C}$	TRET = $+85\text{ }^{\circ}\text{C}$	30	-	-	years
	Data retention (EEPROM data memory) after 300 kcycles at $T_A = 85\text{ }^{\circ}\text{C}$		30	-	-	
	Data retention (program memory) after 10 kcycles at $T_A = 105\text{ }^{\circ}\text{C}$	TRET = $+105\text{ }^{\circ}\text{C}$	10	-	-	
	Data retention (EEPROM data memory) after 300 kcycles at $T_A = 105\text{ }^{\circ}\text{C}$		10	-	-	

1. Guaranteed by characterization results.  
2. Characterization is done according to JEDEC JESD22-A117.

### Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to  $\pm 8$  mA, and sink or source up to  $\pm 20$  mA (with the non-standard  $V_{OL}/V_{OH}$  specifications given in [Table 43](#)).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#):

- The sum of the currents sourced by all the I/Os on  $V_{DD}$ , plus the maximum Run consumption of the MCU sourced on  $V_{DD}$ , cannot exceed the absolute maximum rating  $I_{VDD\Sigma}$  (see [Table 11](#)).
- The sum of the currents sunk by all the I/Os on  $V_{SS}$  plus the maximum Run consumption of the MCU sunk on  $V_{SS}$  cannot exceed the absolute maximum rating  $I_{VSS\Sigma}$  (see [Table 11](#)).

### Output voltage levels

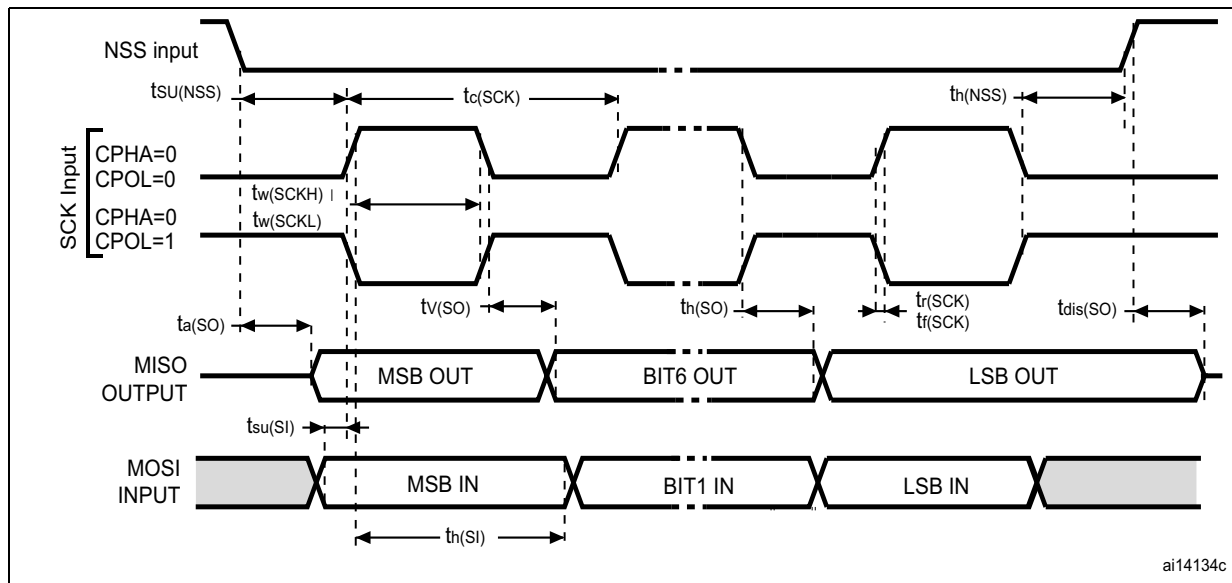
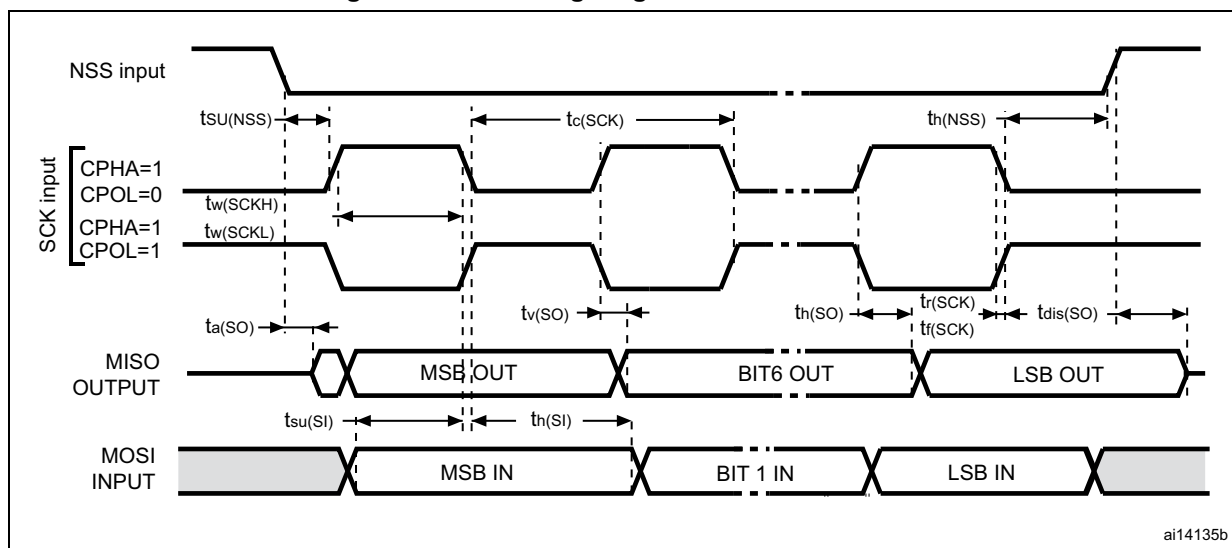
Unless otherwise specified, the parameters given in [Table 43](#) are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in [Table 13](#). All I/Os are CMOS and TTL compliant.

**Table 43. Output voltage characteristics**

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)(2)}$	Output low level voltage for an I/O pin	$I_{IO} = 8$ mA $2.7$ V < $V_{DD}$ < $3.6$ V	-	0.4	V
$V_{OH}^{(3)(2)}$	Output high level voltage for an I/O pin		2.4	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = 4$ mA $1.65$ V < $V_{DD}$ < $2.7$ V	-	0.45	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin		$V_{DD}-0.45$	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = 20$ mA $2.7$ V < $V_{DD}$ < $3.6$ V	-	1.3	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin		$V_{DD}-1.3$	-	

1. The  $I_{IO}$  current sunk by the device must always respect the absolute maximum rating specified in [Table 11](#) and the sum of  $I_{IO}$  (I/O ports and control pins) must not exceed  $I_{VSS}$ .
2. Tested in production.
3. The  $I_{IO}$  current sourced by the device must always respect the absolute maximum rating specified in [Table 11](#) and the sum of  $I_{IO}$  (I/O ports and control pins) must not exceed  $I_{VDD}$ .
4. Guaranteed by characterization results.

Figure 22. SPI timing diagram - slave mode and CPHA = 0

Figure 23. SPI timing diagram - slave mode and CPHA = 1<sup>(1)</sup>

1. Measurement points are done at CMOS levels:  $0.3V_{DD}$  and  $0.7V_{DD}$ .



Table 51. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. <sup>(1)</sup>	Max. <sup>(1)</sup>	Unit
Input levels					
V <sub>DD</sub>	USB operating voltage <sup>(2)</sup>	-	3.0	3.6	V
V <sub>DI</sub> <sup>(3)</sup>	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V <sub>CM</sub> <sup>(3)</sup>	Differential common mode range	Includes V <sub>DI</sub> range	0.8	2.5	
V <sub>SE</sub> <sup>(3)</sup>	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V <sub>OL</sub> <sup>(4)</sup>	Static output level low	R <sub>L</sub> of 1.5 kΩ to 3.6 V <sup>(5)</sup>	-	0.3	V
V <sub>OH</sub> <sup>(4)</sup>	Static output level high	R <sub>L</sub> of 15 kΩ to V <sub>SS</sub> <sup>(5)</sup>	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full speed electrical specification, the USB\_DP (D+) pin should be pulled up with a 1.5 k $\Omega$  resistor to a 3.0-to-3.6 V voltage range.
3. Guaranteed by characterization results.
4. Tested in production.
5.  $R_L$  is the load connected on the USB drivers.

Figure 25. USB timings: definition of data signal rise and fall time

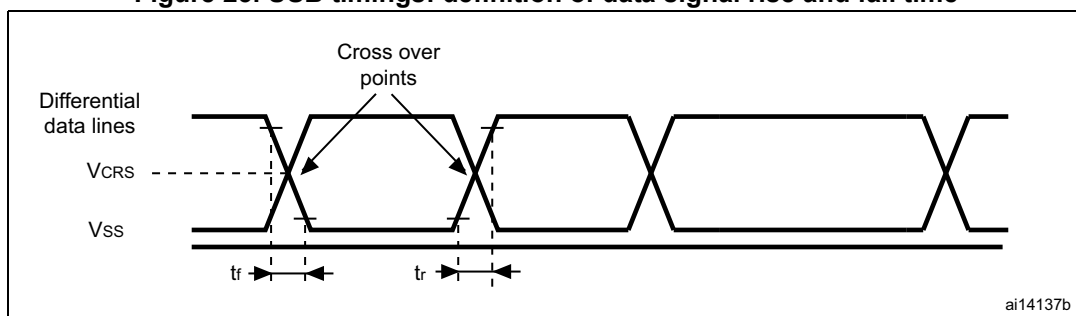
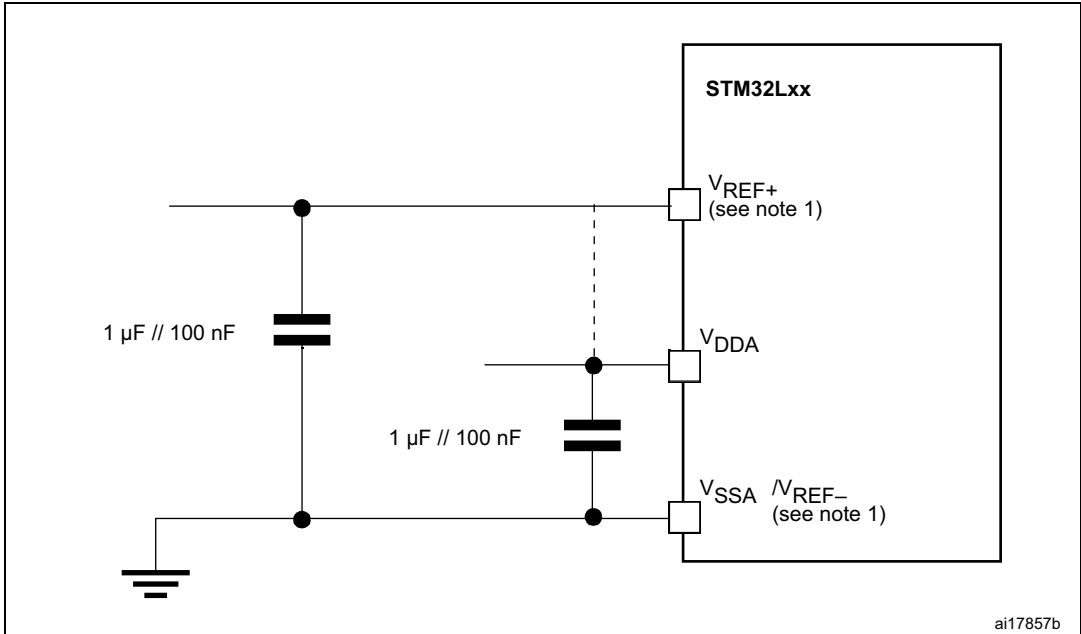


Table 52. USB: full speed electrical characteristics

Driver characteristics <sup>(1)</sup>					
Symbol	Parameter	Conditions	Min	Max	Unit
$t_r$	Rise time <sup>(2)</sup>	$C_L = 50$ pF	4	20	ns
$t_f$	Fall Time <sup>(2)</sup>	$C_L = 50$ pF	4	20	ns
$t_{rfm}$	Rise/ fall time matching	$t_r/t_f$	90	110	%
$V_{CRS}$	Output signal crossover voltage		1.3	2.0	V

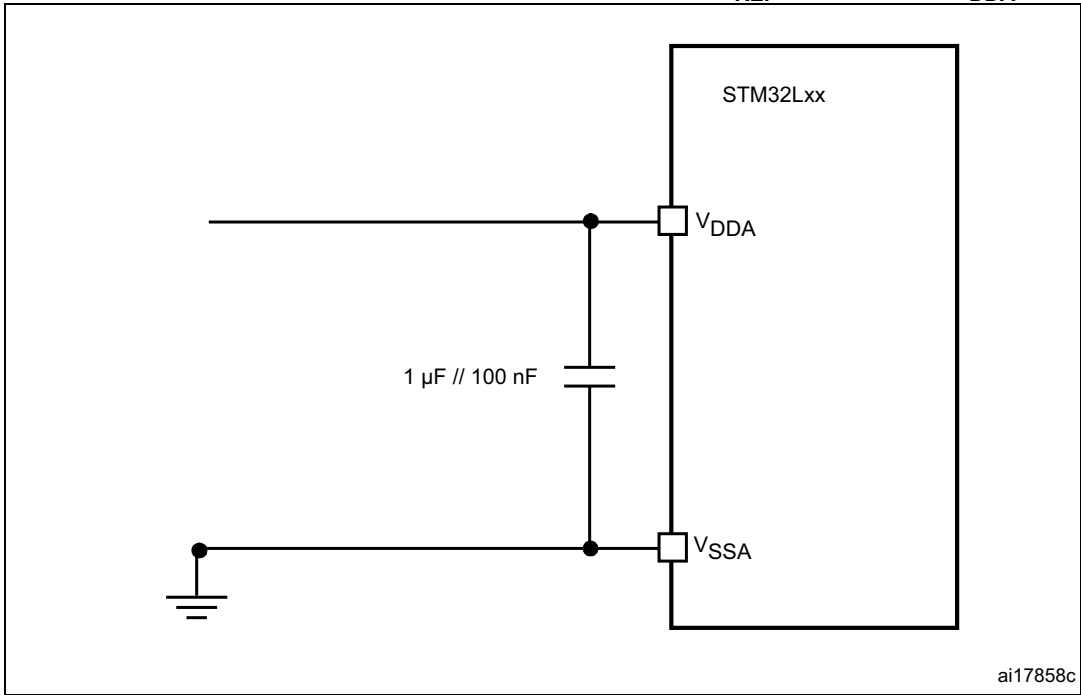
1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

**Figure 29. Power supply and reference decoupling ( $V_{REF+}$  not connected to  $V_{DDA}$ )**



1.  $V_{REF+}$  and  $V_{REF-}$  inputs are available only on 100-pin packages.

**Figure 30. Power supply and reference decoupling ( $V_{REF+}$  connected to  $V_{DDA}$ )**



1.  $V_{REF+}$  and  $V_{REF-}$  inputs are available only on 100-pin packages.

### 6.3.18 DAC electrical specifications

Data guaranteed by design, unless otherwise specified.

**Table 57. DAC characteristics**

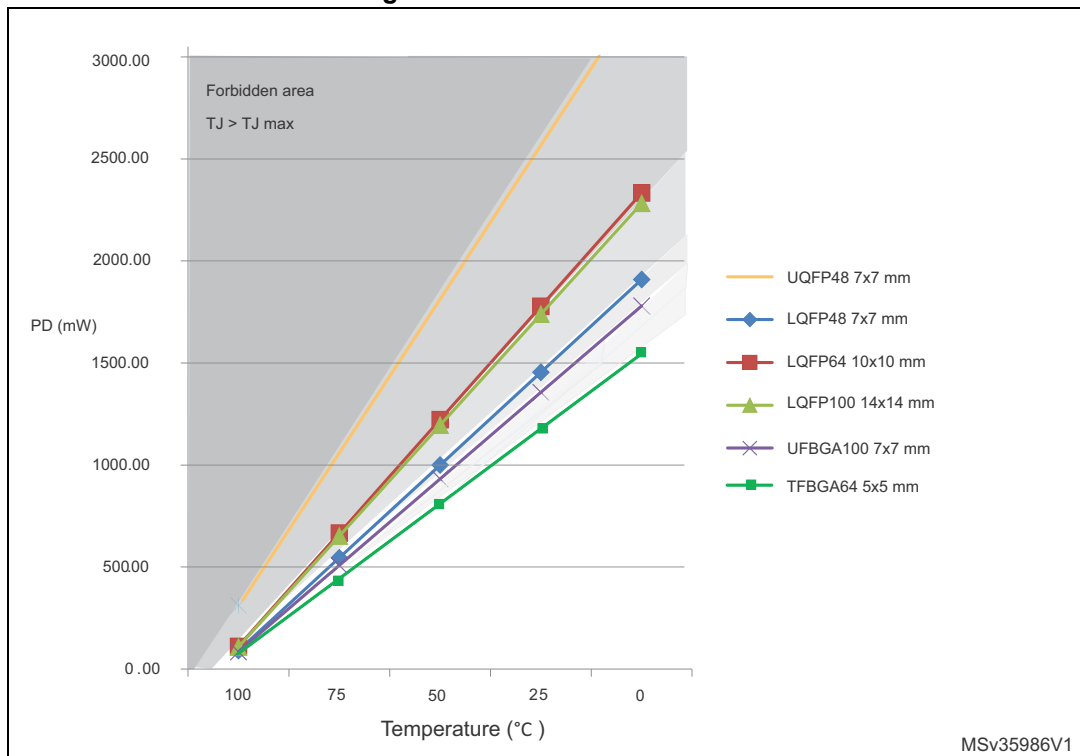
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>DDA</sub>	Analog supply voltage	-		1.8	-	3.6	V
V <sub>REF+</sub>	Reference supply voltage	V <sub>REF+</sub> must always be below V <sub>DDA</sub>		1.8	-	3.6	V
V <sub>REF-</sub>	Lower reference voltage	-		V <sub>SSA</sub>			V
I <sub>DDVREF+</sub> <sup>(1)</sup>	Current consumption on V <sub>REF+</sub> supply V <sub>REF+</sub> = 3.3 V	No load, middle code (0x800)		-	130	220	μA
		No load, worst code (0x000)		-	220	350	μA
I <sub>DDA</sub> <sup>(1)</sup>	Current consumption on V <sub>DDA</sub> supply V <sub>DDA</sub> = 3.3 V	No load, middle code (0x800)		-	210	320	μA
		No load, worst code (0xF1C)		-	320	520	μA
R <sub>L</sub>	Resistive load	DAC output buffer ON	Connected to V <sub>SSA</sub>	5	-	-	kΩ
			Connected to V <sub>DDA</sub>	25	-	-	
C <sub>L</sub>	Capacitive load	DAC output buffer ON		-	-	50	pF
R <sub>O</sub>	Output impedance	DAC output buffer OFF		12	16	20	kΩ
V <sub>DAC_OUT</sub>	Voltage on DAC_OUT output	DAC output buffer ON		0.2	-	V <sub>DDA</sub> − 0.2	V
		DAC output buffer OFF		0.5	-	V <sub>REF+</sub> − 1LSB	mV
DNL <sup>(1)</sup>	Differential non linearity <sup>(2)</sup>	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ DAC output buffer ON		-	1.5	3	LSB
		No R <sub>LOAD</sub> , C <sub>L</sub> ≤ 50 pF DAC output buffer OFF		-	1.5	3	
INL <sup>(1)</sup>	Integral non linearity <sup>(3)</sup>	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ DAC output buffer ON		-	2	4	
		No R <sub>LOAD</sub> , C <sub>L</sub> ≤ 50 pF DAC output buffer OFF		-	2	4	
Offset <sup>(1)</sup>	Offset error at code 0x800 <sup>(4)</sup>	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ DAC output buffer ON		-	±10	±25	
		No R <sub>LOAD</sub> , C <sub>L</sub> ≤ 50 pF DAC output buffer OFF		-	±5	±8	
Offset1 <sup>(1)</sup>	Offset error at code 0x001 <sup>(5)</sup>	No R <sub>LOAD</sub> , C <sub>L</sub> ≤ 50 pF DAC output buffer OFF		-	±1.5	±5	

Table 57. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
dOffset/dT <sup>(1)</sup>	Offset error temperature coefficient (code 0x800)	V <sub>DDA</sub> = 3.3V, T <sub>A</sub> = 0 to 50 °C DAC output buffer OFF	-20	-10	0	μV/°C
		V <sub>DDA</sub> = 3.3V, T <sub>A</sub> = 0 to 50 °C DAC output buffer ON	0	20	50	
Gain <sup>(1)</sup>	Gain error <sup>(6)</sup>	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ DAC output buffer ON	-	+0.1 / -0.2%	+0.2 / - 0.5%	%
		No R <sub>LOAD</sub> , C <sub>L</sub> ≤ 50 pF DAC output buffer OFF	-	+0 / -0.2%	+0 / -0.4%	
dGain/dT <sup>(1)</sup>	Gain error temperature coefficient	V <sub>DDA</sub> = 3.3V, T <sub>A</sub> = 0 to 50 °C DAC output buffer OFF	-10	-2	0	μV/°C
		V <sub>DDA</sub> = 3.3V, T <sub>A</sub> = 0 to 50 °C DAC output buffer ON	-40	-8	0	
TUE <sup>(1)</sup>	Total unadjusted error	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ DAC output buffer ON	-	12	30	LSB
		No R <sub>LOAD</sub> , C <sub>L</sub> ≤ 50 pF DAC output buffer OFF	-	8	12	
t <sub>SETTLING</sub>	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB)	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ	-	7	12	μs
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ	-	-	1	Msp/s
t <sub>WAKEUP</sub>	Wakeup time from off state (setting the ENx bit in the DAC Control register) <sup>(7)</sup>	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ	-	9	15	μs
PSRR+	V <sub>DDA</sub> supply rejection ratio (static DC measurement)	C <sub>L</sub> ≤ 50 pF, R <sub>L</sub> ≥ 5 kΩ	-	-60	-35	dB

1. Guaranteed by characterization results.
2. Difference between two consecutive codes - 1 LSB.
3. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
4. Difference between the value measured at Code (0x800) and the ideal value = V/2.
5. Difference between the value measured at Code (0x001) and the ideal value.
6. Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFFF when buffer is OFF, and from code giving 0.2 V and (V<sub>DDA</sub> - 0.2) V when buffer is ON.
7. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).

Figure 50. Thermal resistance



### 7.7.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from [www.jedec.org](http://www.jedec.org).